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CONT. lower portions 11, 12, and a sidewall 13 therebetween. An active layer 20 is formed on the upper and lower portions 11, 12, and on the sidewall 13. A gate insulation film 30 is formed on a part of the active layer 20 corresponding to the lower portion 12 and on a part of the active layer 20 corresponding to the sidewall 13. A gate electrode 42 is formed on the gate insulation film 30 corresponding to an upper part of the sidewall 13, and an insulation film 41 is formed on a part of the gate insulation film 30 corresponding to the lower portion 12 of the substrate 10 and on a part of the gate insulation film 30 corresponding to a lower part of the sidewall 13 of the substrate 10. Parts of the active layer 20, externally exposed on the upper and lower portions 11, 12 of the substrate 10, are respectively formed as impurity regions 60a and 60b. In addition, an additional insulation film (not shown) is formed on the upper and lower portions 11, 12, and on the sidewall 13.--

IN THE CLAIMS

Please amend the claims as follows:

1. (amended) A thin film transistor, comprising:

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Fig. 2
a stepped substrate forming a single [Z-shaped] cross section provided with a sidewall between upper and lower portions thereof;
an active layer formed on the stepped substrate;
a gate insulation film formed on the active layer;